

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraphs beginning at page 1, line 12 and ending at page 2, line 1 with the following:

A ceramic vessel 1 has a cavity 2 for receiving a solid-state image sensor chip 3. The chip 3 is fixed to the bottom surface of the cavity 2 by a bonding paste 4. The chip 3 has a light receiving surface on which a plurality of light receiving pixels are arranged in a matrix-like manner. A color filter<sub>9</sub>, which associates each of the light receiving pixels with a predetermined color component, is stuck on the light receiving surface to enable color imaging. A plurality of leads are embedded in the vessel 1. One end 6 of each lead is exposed in the cavity 2, while the other end of each lead is exposed at the outer surface of the vessel 1. Each lead end 6 exposed in the cavity 2 is connected to the chip 3 by a wire 5. A transparent glass plate 7 seals the chip 3 in the vessel 1.

The color filter<sub>9</sub> is an organic resin film that covers each light receiving pixel of the chip 3. The resin film is stuck on the surface of the chip 3 and then, in correspondence with each pixel, colored to a predetermined color. When exposed to light, such as sunlight, over a long period of time, the color filter<sub>9</sub> may discolor or fade. This restricts the environment in which the solid-state image sensor may be used.

Please replace the paragraph beginning at page 3, line 23 and ending at page 3, line 28 with the following:

A package structure of a solid-state image sensor according to a preferred embodiment of the present invention will now be described with reference to Figs. 2 to 4. A solid-state image sensor chip 13, to which a color filter<sub>19</sub> is applied, is fixed to a vessel 11 at the bottom surface of a cavity 12 by a bonding paste 14. The vessel 11 and the chip 13 are respectively identical to the conventional vessel 1 and chip 3 shown in Fig. 1. Lead ends 16a are connected to the chip 13 with wires 15.

Please replace the paragraph beginning at page 4, line 33 and ending at page 5, line 8 with the following:

As shown in Fig. 4, the length L of the glass plate 18 is greater than that of the cavity 12 and the width W of the glass plate 18 is less than that of the cavity 12. Thus, when the glass plate 18 is attached to the vessel 11, a gap is formed between the glass plate 18 and the cavity 12 on each side of the glass plate 18. The gaps serve to decrease internal stress that is produced when the resin layer 17 contracts or expands. The width W of the glass plate 18 is at least wider than the light receiving surface of the chip 13.

Please replace the paragraph beginning at page 5, line 16 and ending at page 5, line 19 with the following:

The color filter 19 is protected in the solid-state image sensor of the preferred embodiment. Thus, the solid-state image sensor of the preferred embodiment may be used in a wide variety of environments.

Please replace the paragraph beginning at page 5, line 31 and ending at page 6, line 17 with the following:

The chip 13, which is fabricated through a predetermined fabrication process, is fixed to the bottom surface of the cavity 12 by the bonding paste 14. Then, a plurality of bonding pads (not shown) formed at the ends of the chip 13 and the lead ends 16a exposed in the cavity 12 are electrically connected by wires 15 (e.g., gold wires). Next, a fluxional transparent resin is charged into the cavity 12. The amount of transparent resin is controlled such that the resin covers the chip 13 and the wires 15 but does not flow out of the cavity 12. Before the resin hardens, the surface of the resin, or the cavity 12, is covered by the glass plate 18. The width W of the glass plate 18 is less than that of the cavity 12, and the length L of the glass plate 18 is greater than that of the cavity 12.

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Accordingly, the glass plate 18 is arranged so that a gap is formed between the sides of the glass plate 18 and the opposing walls of the vessel 11. The transparent resin in the cavity 12 is then hardened to form the resin layer 17. The package structure of Fig. 2 that protects the color filter of the chip 13 is obtained in this manner.

Please replace the paragraph beginning at page 6, line 30 and ending at page 7, line 4 with the following:

Light having a relatively short wavelength (ultraviolet light) that causes deterioration of the color filter 19 is absorbed by the resin layer 17. Thus, such light does not reach the color filter 19. As a result, the color filter 19 is protected from light that causes deterioration, and discoloring of the color filter 19 is prevented. A solid-state image sensor having superior durability is therefore obtained.